MITSUBISHI ELECTRIC

<Diode Modules>

RM200DY1-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

dual switch (Cathode Common)

Forward current I_F 200A
Repetitive peak reverse voltage V_{RRM} 1200V
Maximum junction temperature T_{jmax} ..... 150°C

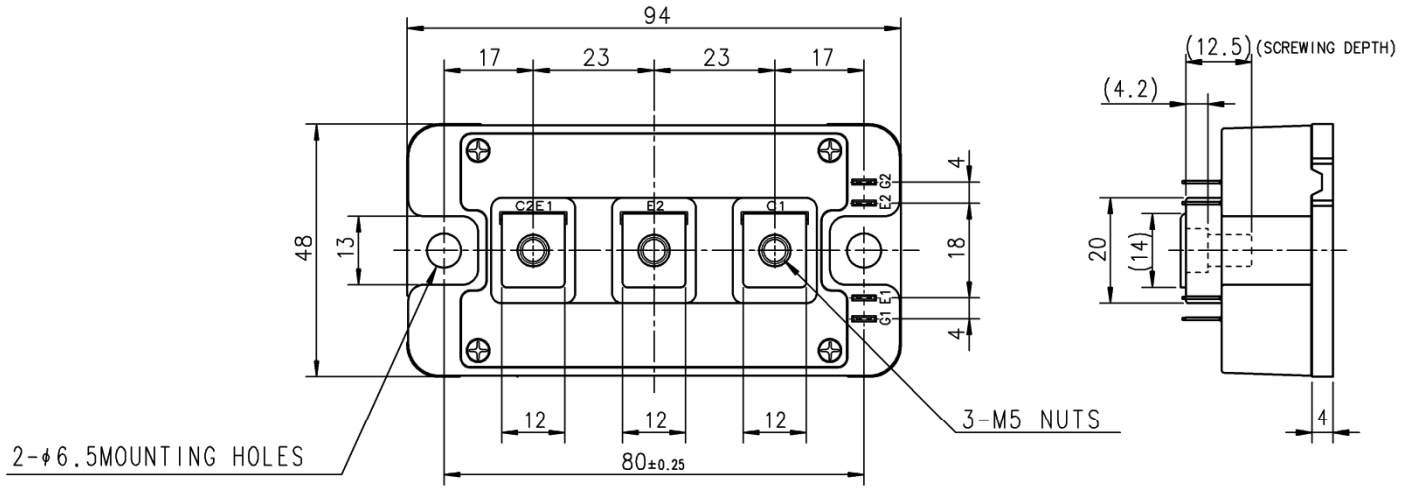
- Flat base Type
- Copper base plate
- RoHS Directive compliant
- Recognized under UL1557, File E323585

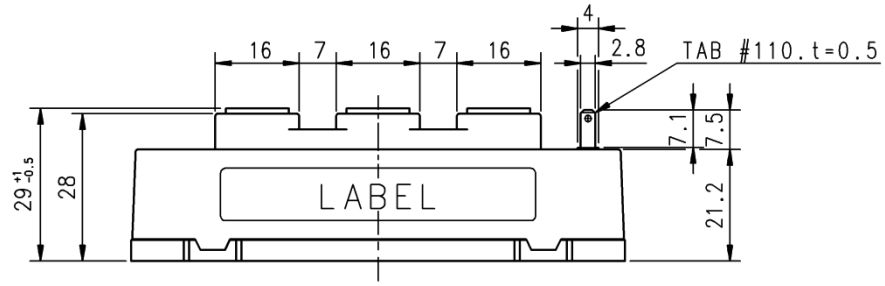
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

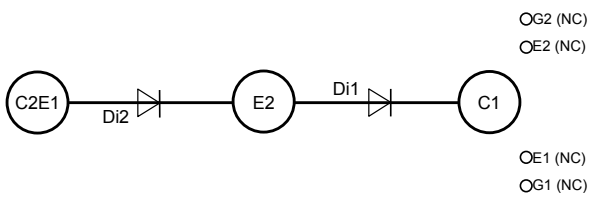
OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm





INTERNAL CONNECTION



Tolerance otherwise specified

Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

RM200DY1-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	-	1200	V
V_{RSM}	Non-repetitive peak reverse voltage	-	1200	V
$V_{R(DC)}$	Reverse DC blocking voltage	-	960	V
I_{DC}	Forward current	DC (Note1)	200	A
I_{FSM}	Surge non-repetitive forward current	1 cycle of half wave at 60Hz, peak value, T_j=25°C start, V_{RM}=0 V	1000	
I^2t	Current square time for fusing	t_w=8.3 ms, T_j=25 °C start, Value for one cycle of surge current	4.16×10^3	A^2s
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T_j	Junction temperature	-	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{RRM}	Reverse current	V_R=V_{RRM}, T_j=25 °C	-	-	1.0	mA
V_F	Forward voltage	I_F=200 A, T_j=25 °C (Note3)	-	3.0	3.8	V
t_{rr}	Reverse recovery time	V_{RM}=600 V, I_F=200 A, T_j=25 °C, di/dt=-5500 A/μs, Inductive load	-	-	150	ns
Q_{rr}	Reverse recovery charge		-	9.0	-	μC
E_{rr}	Reverse recovery energy per pulse	T_j=125 °C, Inductive load	-	14.3	-	mJ

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance	Junction to case, per Diode (Note2)	-	-	170	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1/2 module, Thermal grease applied (Note2, 4)	-	22	-	K/kW

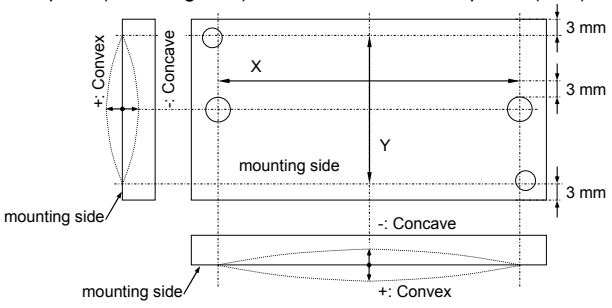
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 5 screw	2.5	3.0	3.5	N·m
M_s		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
m	mass	-	-	310	-	g
e_c	Flatness of base plate	On the centerline X, Y (Note5)	-100	-	+100	μm

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

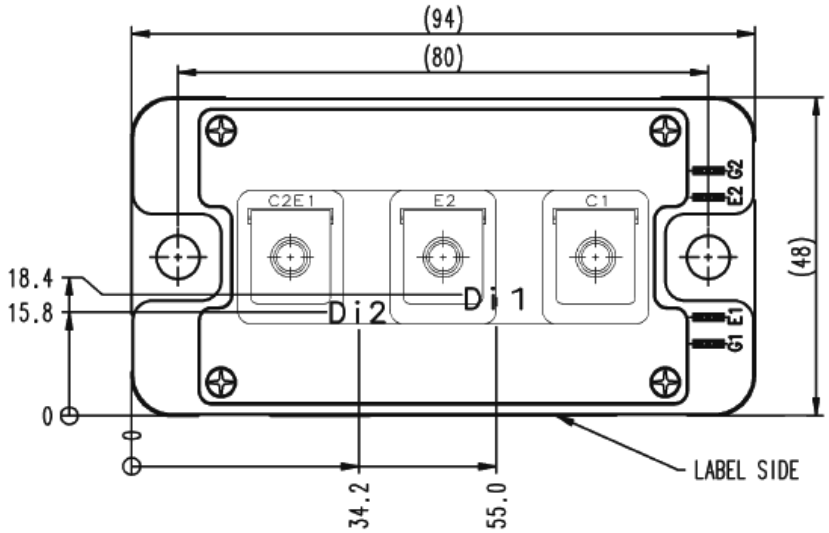
Note1. Junction temperature (T_j) should not increase beyond T_{jmax} rating.

2. Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.The heat sink thermal resistance should measure just under the chips.
3. Pulse width and repetition rate should be such as to cause negligible temperature rise.
4. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).
5. Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



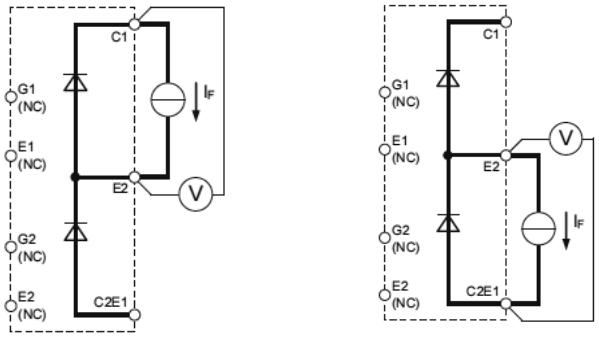
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm



Di1/Di2: DIODE

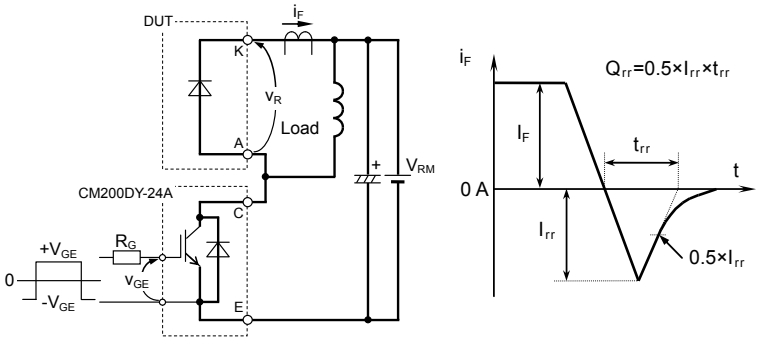
TEST CIRCUIT



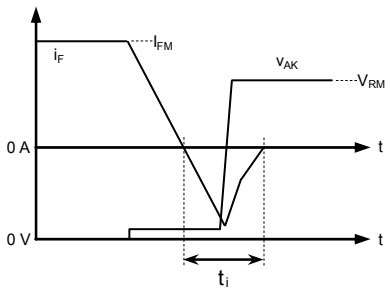
Di1 Di2

V_F test circuit

TEST CIRCUIT AND WAVEFORMS



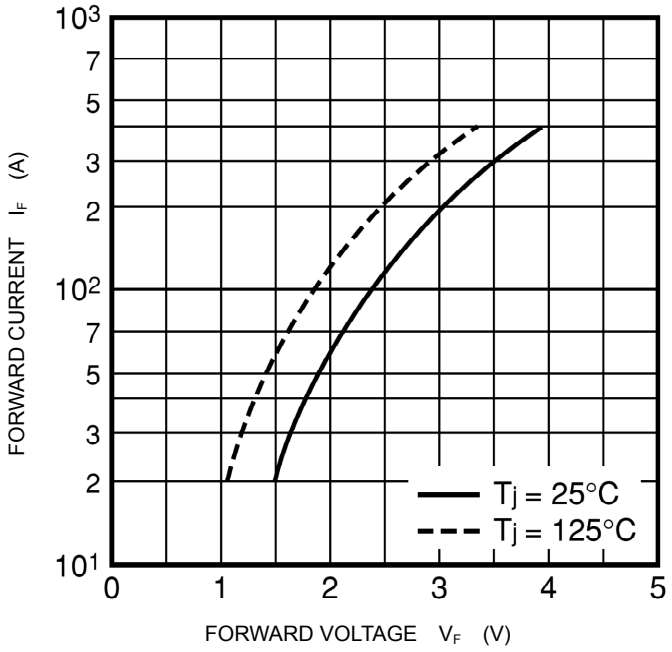
Reverse recovery characteristics test circuit and waveforms



Reverse recovery energy test waveforms
(Integral time instruction drawing)

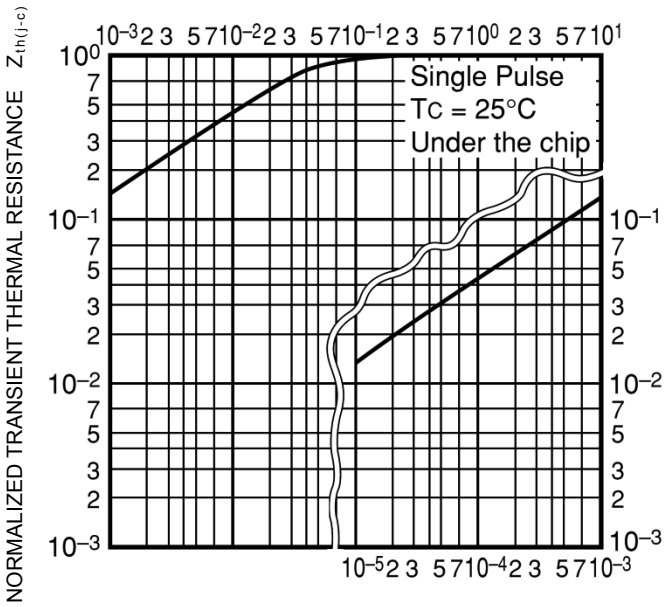
PERFORMANCE CURVES

FORWARD CHARACTERISTICS
(TYPICAL)



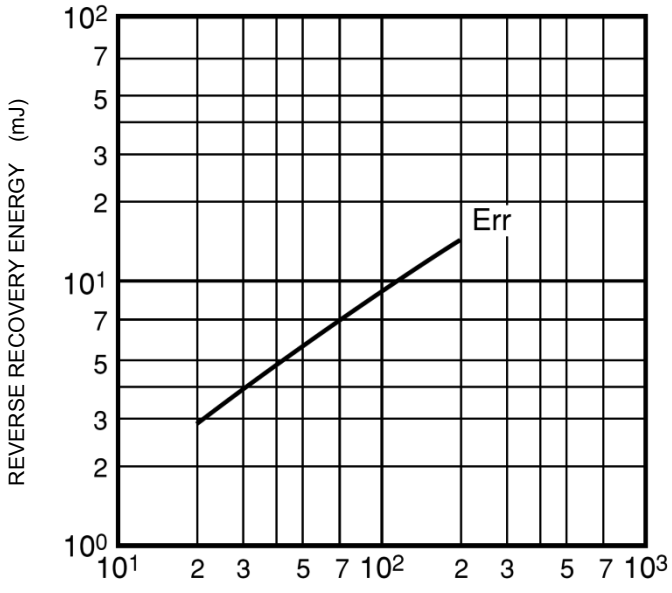
TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS
(MAXIMUM)

$R_{th(j-c)}$=170 K/kW



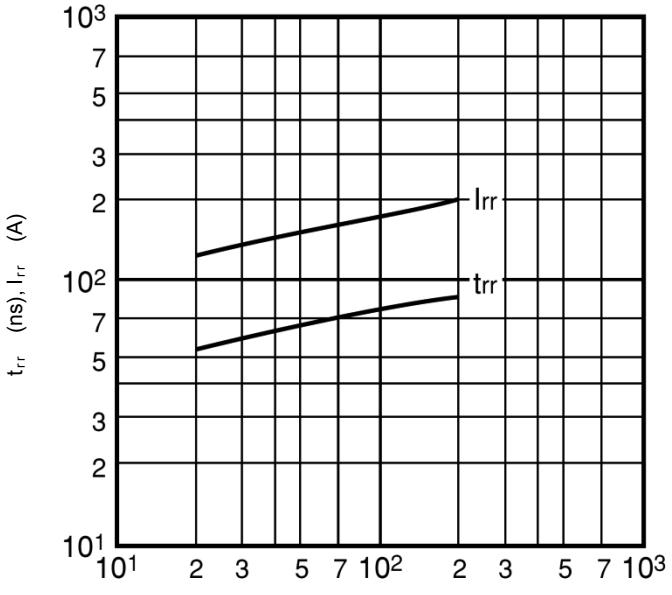
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

V_R=600 V, di/dt=-5500 A/μs, T_j=125 °C,
INDUCTIVE LOAD, PER PULSE



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

V_R=600 V, di/dt=-5500 A/μs, T_j=25 °C,
INDUCTIVE LOAD



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